

2SK1402, 2SK1402A

Silicon N Channel MOS FET

REJ03G0942-0200

(Previous: ADE-208-1282)

Rev.2.00 Sep 07, 2005

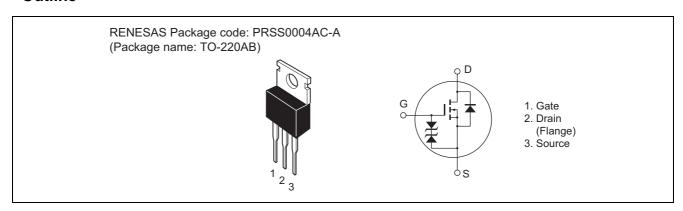
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item		Symbol	Ratings	Unit	
Drain to source voltage	n to source voltage 2SK1402		600	V	
	2SK1402A		650		
Gate to source voltage		V_{GSS}	±30	V	
Drain current		I _D	4	А	
Drain peak current		I _{D(pulse)} *1	16	А	
Body to drain diode reverse drain current		I _{DR}	4	А	
Channel dissipation		Pch*2	50	W	
Channel temperature		Tch	150	°C	
Storage temperature		Tstg	-55 to +150	°C	

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at $T_C = 25$ °C

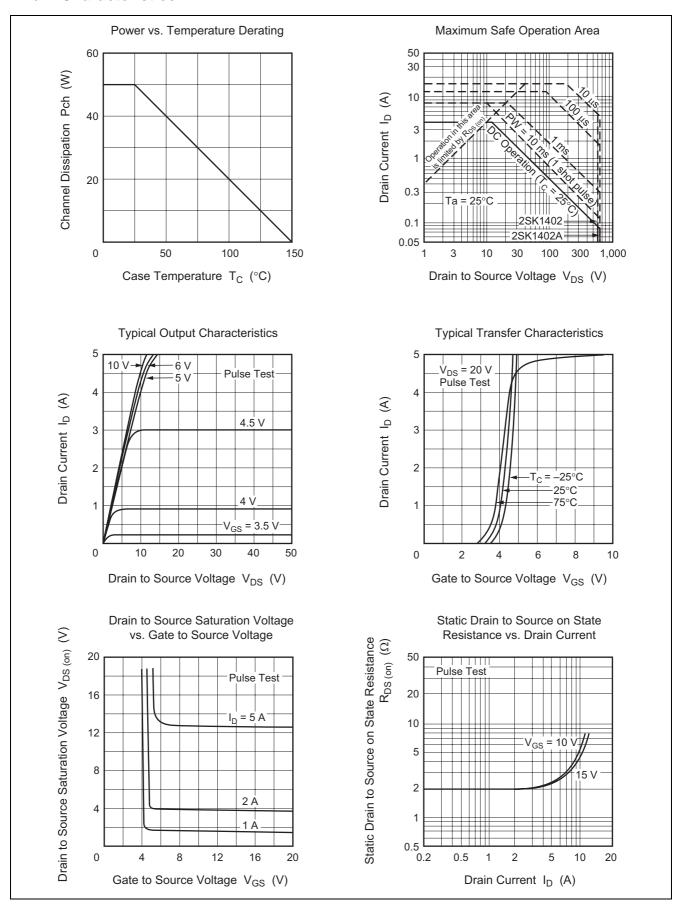
Electrical Characteristics

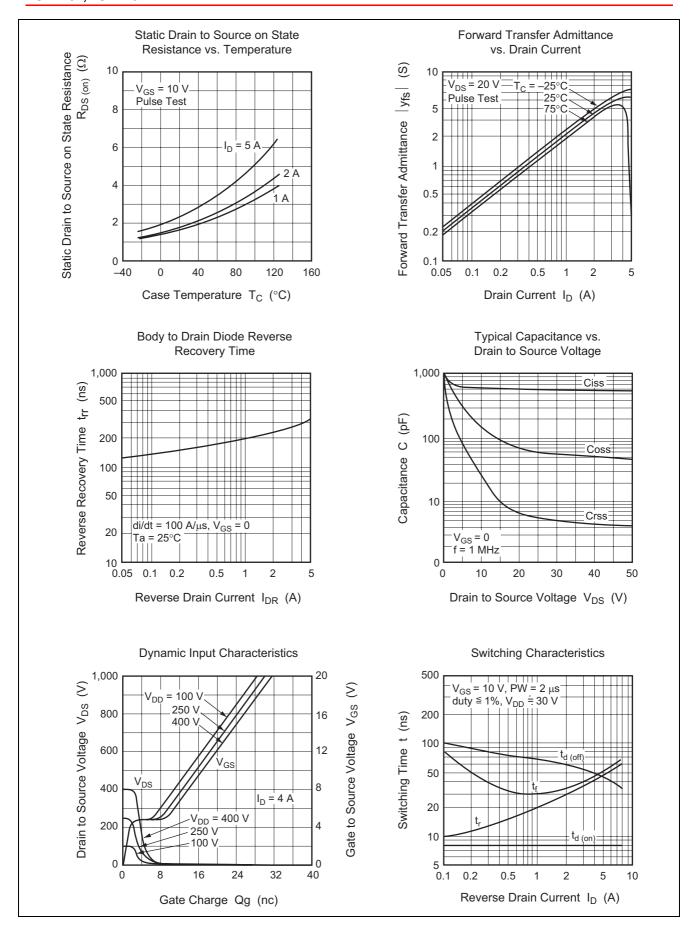
 $(Ta = 25^{\circ}C)$

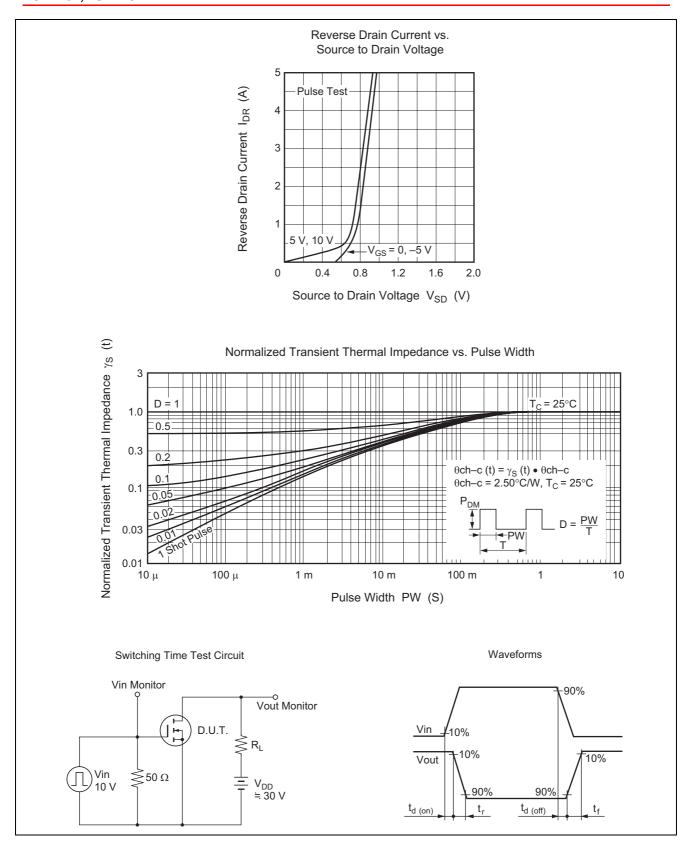
Item		Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source	2SK1402	$V_{(BR)DSS}$	600	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
breakdown voltage	2SK1402A		650	_	_		
Gate to source breakdown voltage		$V_{(BR)GSS}$	±30	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current		I _{GSS}		_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain	2SK1402	I _{DSS}	_	_	250	μΑ	$V_{DS} = 500 \text{ V}, V_{GS} = 0$
current	2SK1402A	1					$V_{DS} = 550 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	2.0	_	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on	2SK1402	R _{DS(on)}		1.8	2.4	Ω	$I_D = 2 A$, $V_{GS} = 10 V^{*3}$
state resistance	2SK1402A			2.0	2.6		
Forward transfer admittance		y _{fs}	2.2	3.5	_	S	$I_D = 2 A$, $V_{DS} = 10 V^{*3}$
Input capacitance		Ciss		600	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance		Coss		140	_	pF	f = 1 MHz
Reverse transfer capacitance		Crss		25	_	pF	
Turn-on delay time		t _{d(on)}		8	_	ns	$I_D = 2 A$, $V_{GS} = 10 V$,
Rise time		t _r		30	_	ns	$R_L = 15 \Omega$
Turn-off delay time		$t_{d(off)}$		60	_	ns	
Fall time		t _f	_	35	_	ns	
Body to drain diode forward voltage		V_{DF}	_	0.9	_	V	$I_F = 4 A, V_{GS} = 0$
Body to drain diode reverse recovery		t _{rr}	_	300	_	ns	$I_F = 4 \text{ A}, V_{GS} = 0,$
time							$di_F/dt = 100 A/\mu s$

Note: 3. Pulse test

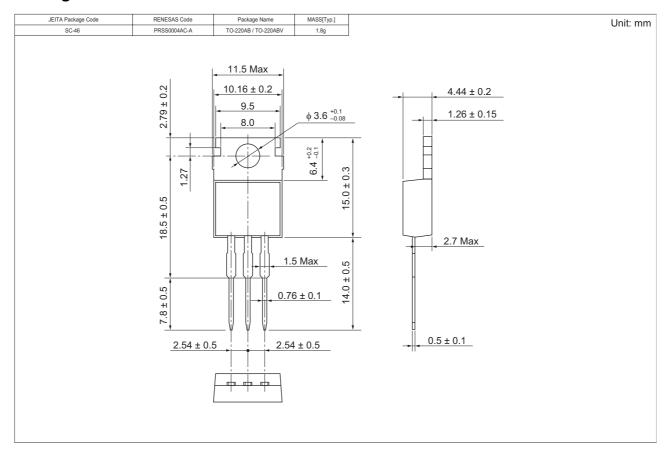
Main Characteristics







Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container		
2SK1402-E	500 pcs	Box (Sack)		
2SK1402A-E	500 pcs	Box (Sack)		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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